

FAST RECOVERY EPITAXIAL DIODE

200V / 30A V_F=1.0V@I_F=30A, trr=35ns

TO-247AC Modified

PRODUCT FEATURES

- Ultrafast Recovery Time
- Soft Recovery Characteristics
- Low Recovery Loss
- Low Forward Voltage
- High Surge Current Capability
- Low Leakage Current

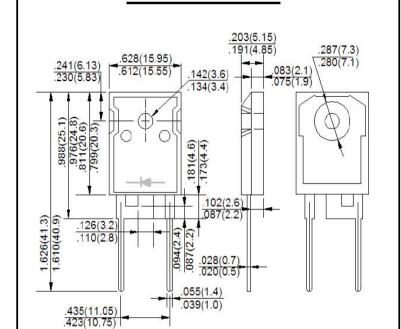
APPLICATIONS

- Freewheeling, Snubber, Clamp
- Inversion Welder
- Plating Power Supply
- Ultrasonic Cleaner and Welder

MECHANICAL DATA

Case : TO-247AC Modified Molded Plastic
 Epoxy : UL94V-0 rate flame retadant

Polarity: As Marked



Dimensions in inches and (millimeter)

ABSOLUTE MAXIMUM RATINGS (T_c=25°C unless otherwise specified)

PARAMETER Maximum Repetitive Reverse Voltage		SYMBOL	VALUES D30A02EP 200	UNIT V
		Marking		
		VRM		
Average Forward Current	T _C =100°C	lF(AV)	30	Α
RMS Forward Current	T _C =100°C	IF(RMS)	52	Α
Non-Repetitive Surge Forward Current	t _P =10ms, 50Hz, Half Sine Wave	IFSM	300	Α
Power Dissipation		PD	156	W
Operating Junction and Storage Temperatures		Т _Ј , Тѕтс	-55 to + 150	°C
Thermal Resistance	Junction-to-Case	Rejc	0.8	°C/W
Module-to-Sink			1.1	Nt.m
Weight			6.0	g

ELECTRICAL AND DYNAMIC RECOVERY CHARACTERISTICS (T_J=25°C, unless otherwise specified)

TEST CONDITIONS	SYMBOL	Min.	Тур.	Max.	UNIT
VR=200V	I _{RM}	125	¥	25	μΑ
V _R =200√, T _J =125°C		1-10	-	250	uA
IF=30A	VF	(= 0)	0.85	1.0	V
I⊧=30√, TJ=125°C		(= 0)	-	0.95	V
IF=1A, VR=30V, diF/dt=-200A/µs	trr	1 - 6	25	32	ns
V_R =100 V , I_F =30 A di _F /dt=-200 A / μ s, T_J =25 $^{\circ}$ C	trr	1 - 6	35	-	ns
	IRRM		35	-	Α
V _R =100V, I _F =30A di _F /dt=-200A/µs, TJ=125°C	trr		48	-	ns
	IRRM	170	4.2		Α
	VR=200V VR=200V, TJ=125°C IF=30A IF=30V, TJ=125°C IF=1A, VR=30V, diF/dt=-200A/μs V _R =100V, I _F =30A di _F /dt=-200A/μs, TJ=25°C V _R =100V, I _F =30A	VR=200V VR=200V, TJ=125°C IF=30A IF=30V, TJ=125°C VF IF=1A, VR=30V, diF/dt=-200A/µs VR=100V, IF=30A diF/dt=-200A/µs, TJ=25°C VR=100V, IF=30A VR=100V, IF=30A VR=100V, IF=30A VR=100V, IF=30A VR=100V, IF=30A VR=100V, IF=30A	V _R =200V, T _J =125°C I _F =30A I _F =30V, T _J =125°C I _F =30V, T _J =125°C V _F I _F =1A, V _R =30V, diF/dt=-200A/µs V _R =100V, I _F =30A di _F /dt=-200A/µs, T _J =25°C V _R =100V, I _F =30A di _F /dt=-200A/µs, T _J =25°C V _R =100V, I _F =30A di _F /dt=-200A/µs, T _J =25°C	VR=200V VR=200V, TJ=125°C IF=30A IF=30V, TJ=125°C IF=30V, TJ=125°C VF VF	VR=200V I _{RM} - - 25 VR=200V, TJ=125°C - - 250 IF=30A VF - 0.85 1.0 IF=30V, TJ=125°C - - 0.95 IF=1A, VR=30V, diF/dt=-200A/µs trr - 25 32 V _R =100V, I _F =30A trr - 35 - di _F /dt=-200A/µs, TJ=25°C I _{RRM} - 35 - V _R =100V, I _F =30A trr - 48 - di _I (dt=-200A/µs, TJ=125°C trr - 48 -



FIG. 1 - Typical Forward Voltage Drop Characteristics 60 I_F - Forward Current (A) 50 40 30 T_J=125℃ 20 T_J=25℃ 10 0 0 0.2 0.4 0.6 8.0 1.2 V_F - Forward Voltage Drop Voltage (V)

FIG. 2 - Typical Value of Reverse Current vs. Reverse Voltage 100 IR - Reverse Current (uA) 10 T₁=125°C 1 T_J=100°C T_J=150°C 0.1 0.01 T_J=25℃ 0.001 50 100 150 200 V_R - Reverse Voltage (V)

FIG. 3 - Typical Junction Capacitance vs.

Reverse Voltage

1000

100

100

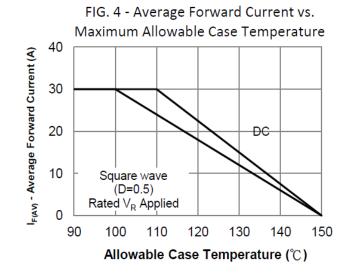
50

100

150

200

V_R - Reverse Voltage (V)



The cruve graph is for reference only, can't be the basis for judgment(曲线图仅供参考)!